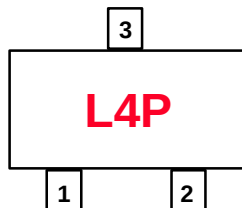


BAT54/A/C/S

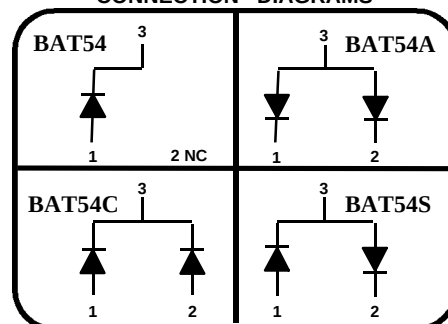
DISCRETE POWER AND SIGNAL
TECHNOLOGIES

PACKAGE
SOT-23
TO-236AB (Low)



MARKING
BAT54 L4P BAT54C L43
BAT54A L42 BAT54S L44

CONNECTION DIAGRAMS



Schottky Barrier Diode

Sourced from Process KA

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Sym	Parameter	Value	Units
T_{stg}	Storage Temperature	-55 to +150	°C
T_J	Operating Junction Temperature	+150	°C
W_{IV}	Working Inverse Voltage	25	V
I_F	DC Forward Current (I_F)	200	mA
i_f	Recurrent Peak Forward Current (I_{FRM})	300	mA
$i_{F(surge)}$	Peak Forward Surge Current (I_{FSM}) Pulse Width = 1.0 Second	600	mA
P_D	Total Power Dissipation at 25°C	230	mW
	Theta ($R_{th j-a}$) (Note 1)	430	°K/W

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

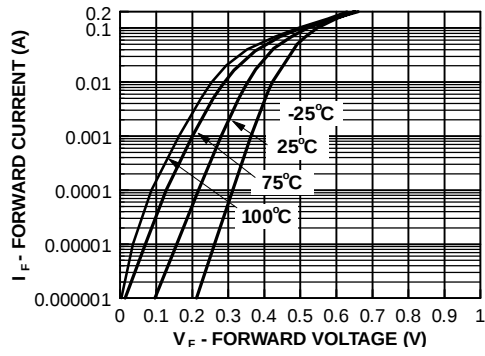
NOTES:

1) From junction to ambient mounted on a ceramic substrate of 10 mm x 8 mm x 0.6 mm

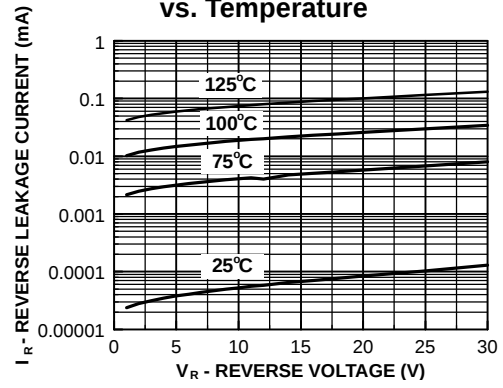
Electrical Characteristics TA = 25°C unless otherwise noted

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
B_V	Breakdown Voltage	30		V	$I_R = 10 \mu A$
I_R	Reverse Leakage		2.0	μA	$V_R = 25 V$
V_F	Forward Voltage		240 320 400 500 1.0	mV mV mV mV V	$I_F = 100 \mu A$ $I_F = 1.0 mA$ $I_F = 10 mA$ $I_F = 30 mA$ $I_F = 100 mA$
C_T	Capacitance		10	pF	$V_R = 1.0 V$ $f = 1.0 MHz$
T_{RR}	Reverse Recovery Time		5.0	ns	$I_F = I_R = 10 mA$ $I_{RR} = 1.0 mA$ $R_L = 100 Ohms$

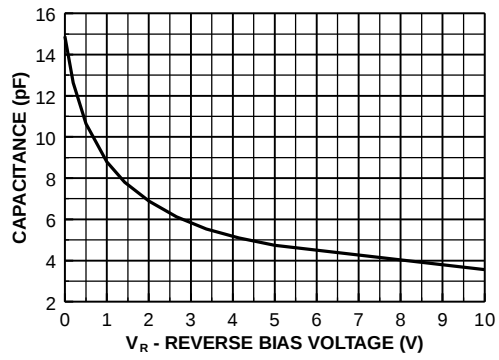
**Forward Voltage
vs. Temperature**

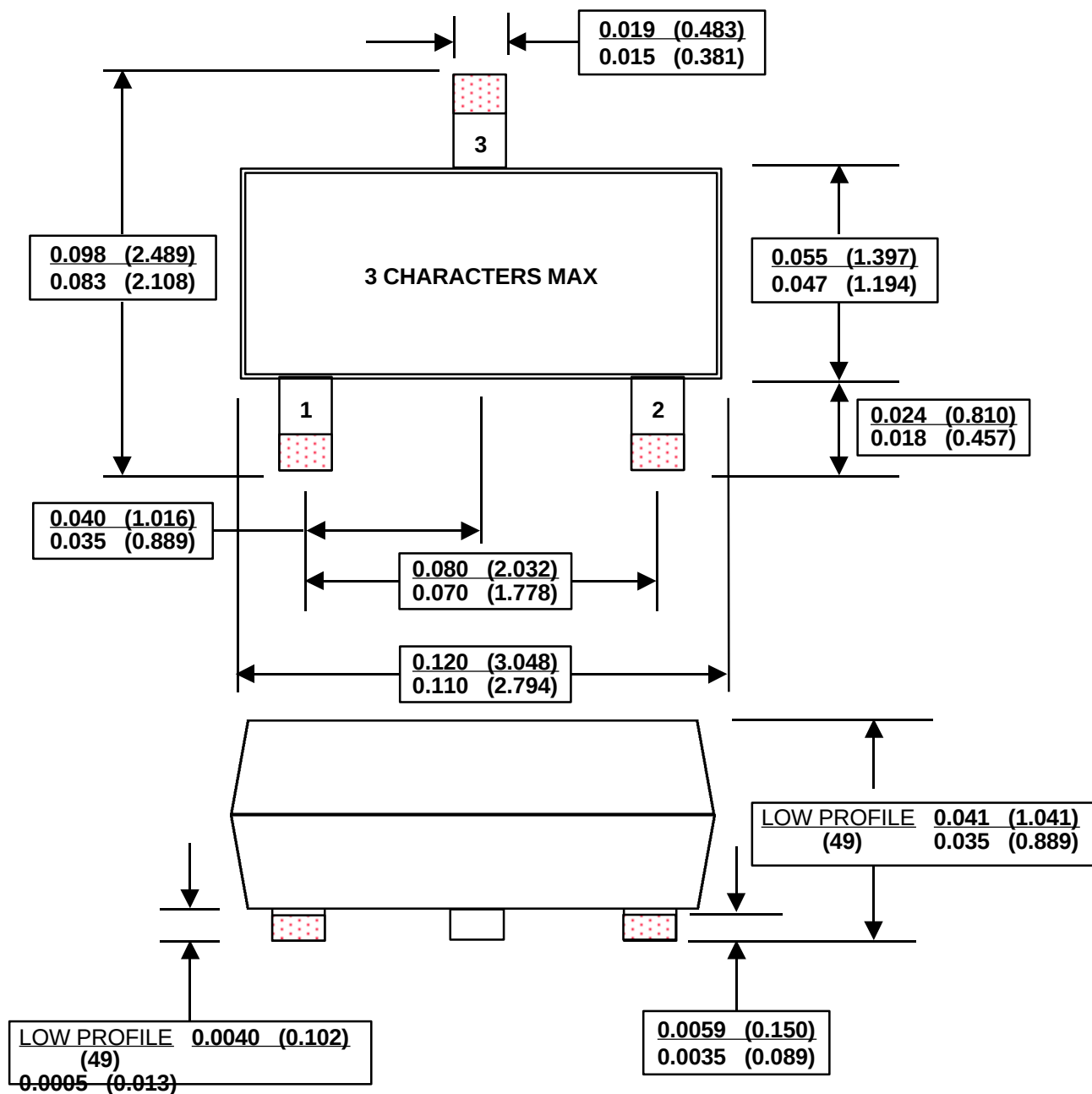


**Reverse Leakage Current
vs. Temperature**

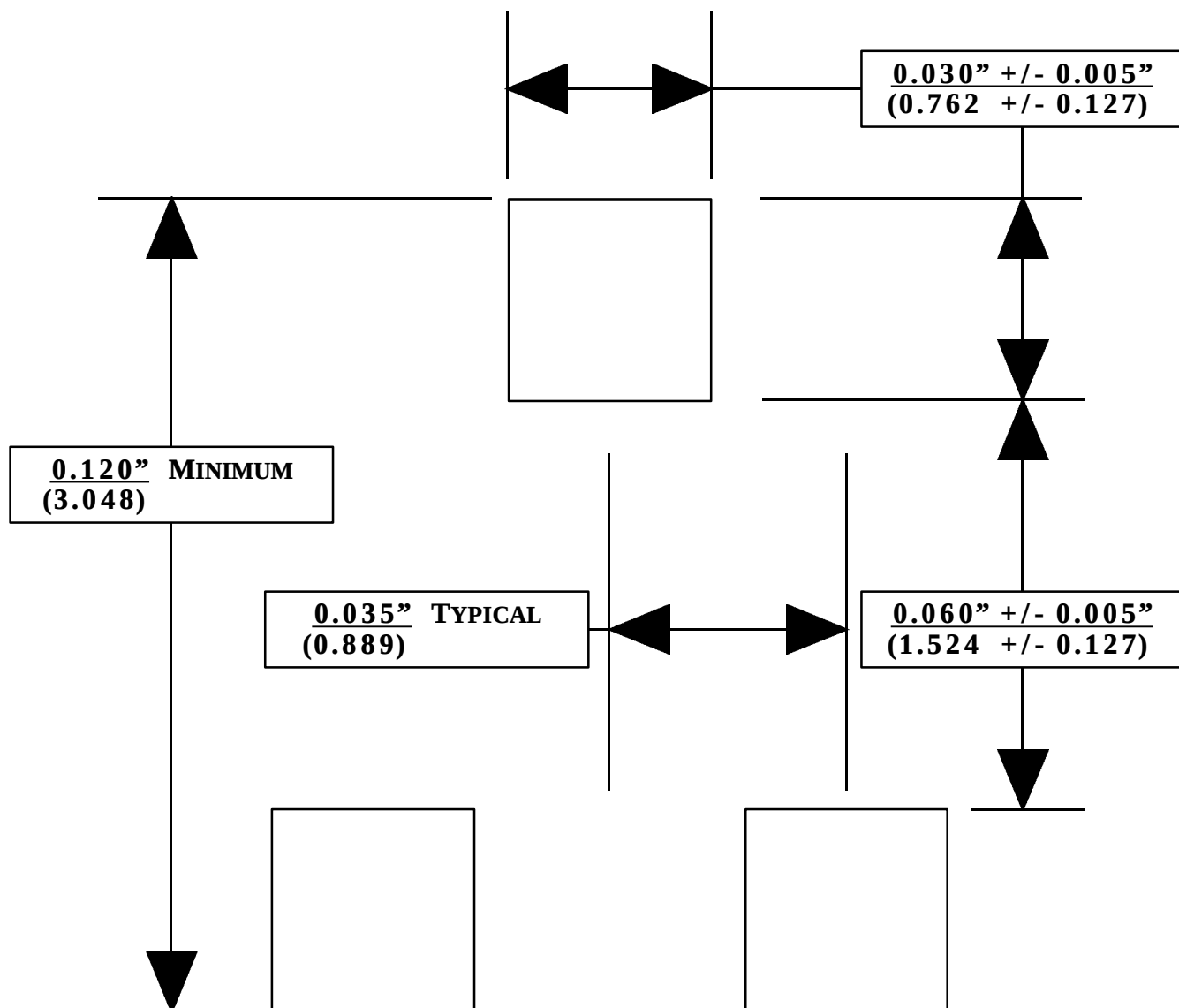


**Capacitance
vs. Reverse Bias Voltage**

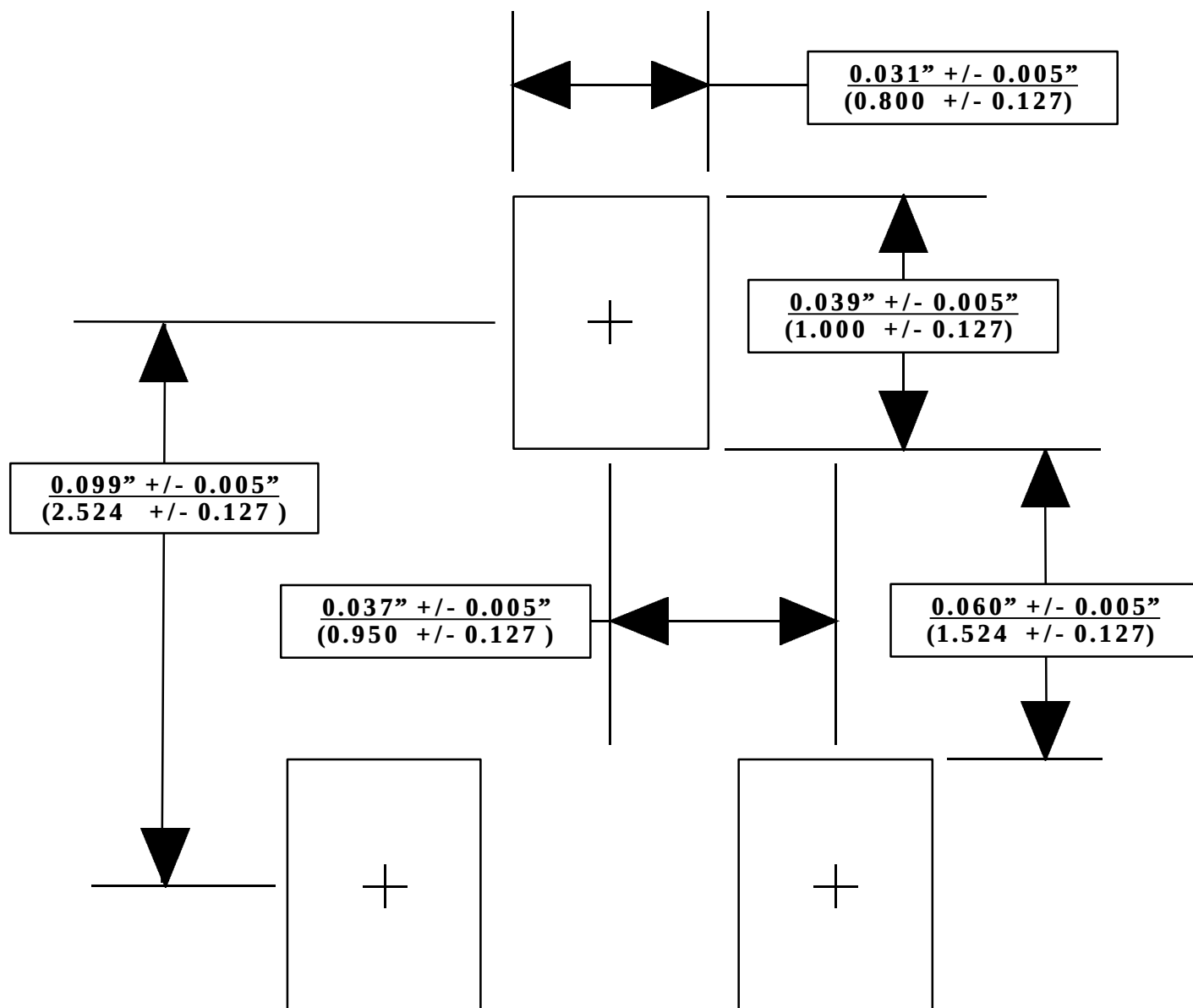




SOT-23
TO-236AB (LOW PROFILE)
22-August-1994



**RECOMMENDED SOLDER PADS
FOR
SOT-23**



**RECOMMENDED SOLDER PADS
FOR
U.S. & European SOT-23
&
Japanese SC-59**